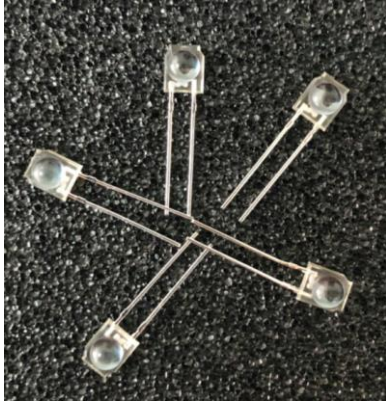


Silicon photodiode

OSD10784



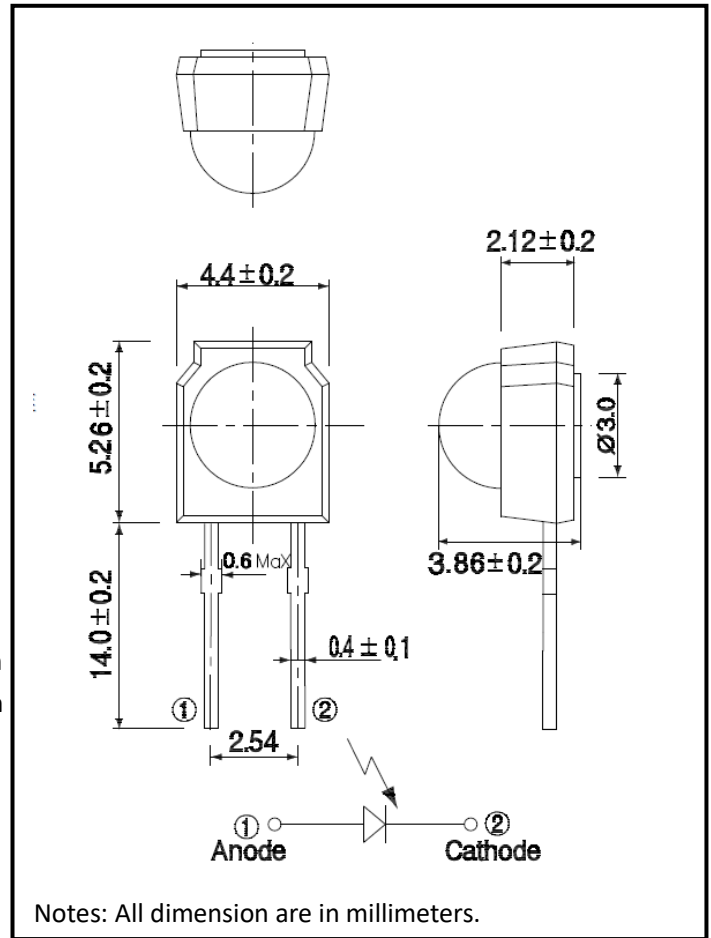
Description

The OSD10784 is IR response high-output, high-speed silicon Photodiode which is mounted in plastic package with $\Phi 3\text{mm}$ Lens.

Applications

- * Laser detect
- * Medical equipment

Absolute Maximum Ratings



Parameter	Symbol	Condition	Min.	Typ.	Max.	Unit
Chip size	size	-	3.05*3.05			mm ²
Active area	A	-	2.794*2.794			mm ²
Dark current	I _D	V _R =100mV		15		pA
		V _R =10V		25		
Rise time	t _R	V _R =0V; λ =635nm; R _L =50Ω		80		ns
Tempcoeffi-cient of I _D	T _{CD}			0.18		times/°C
Reverse breakdown voltage	V _{(BR)R}	I _R =100uA E _v =0mw/cm ²	35			V
Junction Capacitance	C _J	V _R =0V f=1MHz E _e =0mW/cm ²		70		pF
		V _R =10V f=1MHz E _e =0mW/cm ²		25		
Photo sensitivity	S _R	650nm		0.38		A/W
Spectral Application Range	λ range		350		1100	nm
Spectral Response-Peak	λ _p			940		nm
Shunt resistance	R _{sh}	V _R =10mV		0.5		GΩ
Angular Resp 50% Resp Pt	θ ^{1/2}			±30		Degrees

Information in this technical datasheet is believed to be correct and reliable. However, no responsibility is assumed for possible inaccuracies or omission.

Specifications are subject change without notice.

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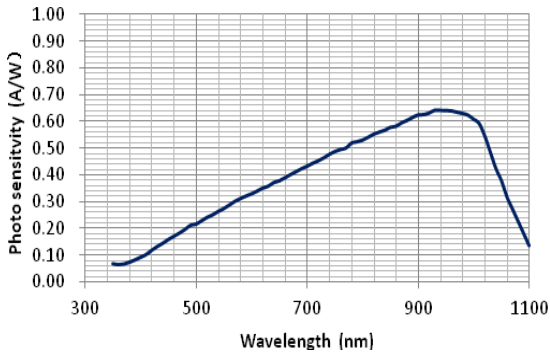
TEL:+86-21-54971821

FAX:+86-21-54971823

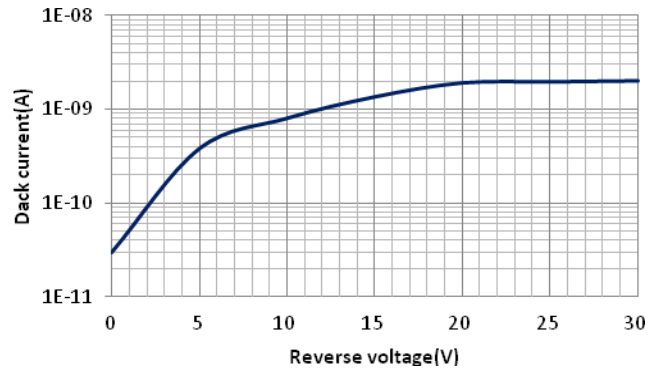
EMAIL: otron.sensor@gmail.com

<http://www.e-otron.com>

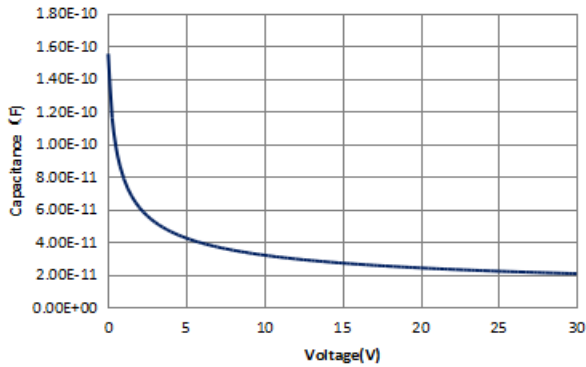
SPECTRAL RESPONSE (Ta=23°C)



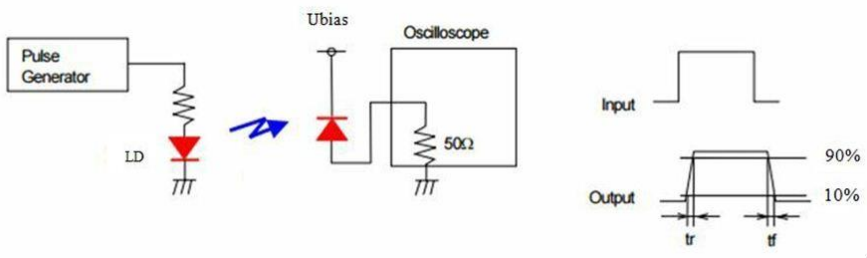
DARK CURRENT VS. REVERSE VOLTAGE (Ta=23°C)



CAPACITANCE VS. REVERSE VOLTAGE (Ta=23°C)



* Response Time Measure Circuit:



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